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FAIRCHILD SEMICONDUCTOR®

July 2008

FDP032N08

N-Channel PowerTrench® MOSFET

75V, 235A, 3.2mΩ

Features

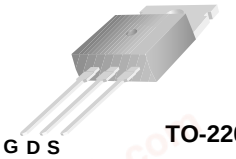
- $R_{DS(on)}$ = 2.5mΩ (Typ.)@ V_{GS} = 10V, I_D = 75A
- Fast switching speed
- Low gate charge
- High performance trench technology for extremely low $R_{DS(on)}$
- High power and current handling capability
- RoHS compliant

Description

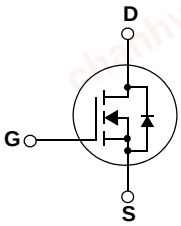
This N-Channel MOSFET is produced using Fairchild Semiconductor's adcanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

Application

- DC to DC convertors / Synchronous Rectification



TO-220



MOSFET Maximum Ratings T_C = 25°C unless otherwise noted*

Symbol	Parameter		FDP032N08	Units
V_{DSS}	Drain to Source Voltage		75	V
V_{GSS}	Gate to Source Voltage		±20	V
I_D	Drain Current - Continuous (T_C = 25°C, Silicon Limited)		235*	A
	- Continuous (T_C = 100°C, Silicon Limited)		165*	A
	- Continuous (T_C = 25°C, Package Limited)		120	A
I_{DM}	Drain Current - Pulsed	(Note 1)	940	A
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	1995	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	5.5	V/ns
P_D	Power Dissipation (T_C = 25°C)		375	W
	- Derate above 25°C		2.5	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +175	°C
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		300	°C

*Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 120A.

Thermal Characteristics

Symbol	Parameter	Ratings	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.4	°C/W
$R_{\theta CS}$	Thermal Resistance, Case to Sink Typ.	0.5	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62.5	

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Package Marking and Ordering Information $T_C = 25^oC$ unless otherwise noted

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDP032N08	FDP032N08	TO-220	-	-	50

Electrical Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V, $T_C = 25^oC$	75	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250μA, Referenced to 25^oC	-	0.05	-	$V/^oC$
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 75V, V_{GS} = 0V	-	-	1	μA
		V_{DS} = 75V, $T_C = 150^oC$	-	-	500	
I_{GSS}	Gate to Body Leakage Current	V_{GS} = ±20V, V_{DS} = 0V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, I_D = 250μA	2.5	3.5	4.5	V
$R_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10V, I_D = 75A	-	2.5	3.2	mΩ
g_{FS}	Forward Transconductance	V_{DS} = 10V, I_D = 75A (Note 4)	-	180	-	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz	-	11400	15160	pF
C_{oss}	Output Capacitance		-	1360	1810	pF
C_{rss}	Reverse Transfer Capacitance		-	595	800	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	V_{DS} = 60V, I_D = 75A, V_{GS} = 10V (Note 4, 5)	-	169	220	nC
Q_{gs}	Gate to Source Gate Charge		-	60	-	nC
Q_{gd}	Gate to Drain “Miller” Charge		-	47	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 37.5V, I_D = 75A, R_{GEN} = 25Ω, V_{GS} = 10V (Note 4, 5)	-	230	470	ns
t_r	Turn-On Rise Time		-	191	392	ns
$t_{d(off)}$	Turn-Off Delay Time		-	335	680	ns
t_f	Turn-Off Fall Time		-	121	252	ns
Drain-Source Diode Characteristics						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	235	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	940	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_{SD} = 75A	-	-	1.3	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0V, I_{SD} = 75A, dI_F/dt = 100A/μs (Note 4)	-	53	-	ns
Q_{rr}	Reverse Recovery Charge		-	77	-	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. L = 0.71mH, I_{AS} = 75A, V_{DD} = 50V, R_G = 25Ω, Starting $T_J = 25°C$
3. $I_{SD} \le 75A$, $di/dt \le 200A/\mu s$, $V_{DD} \le BV_{DSS}$, Starting $T_J = 25°C$
4. Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%
5. Essentially Independent of Operating Temperature Typical Characteristics

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Typical Performance Characteristics

Figure 1. On-Region Characteristics

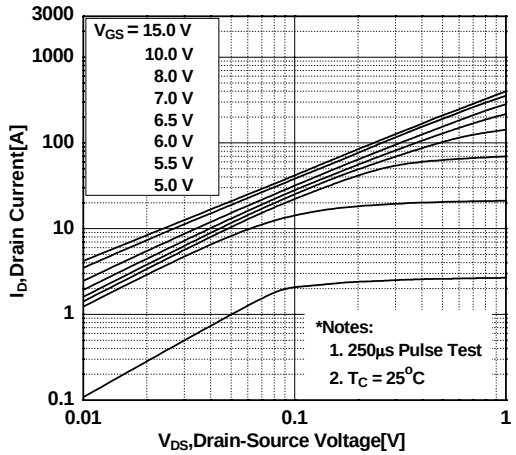


Figure 2. Transfer Characteristics

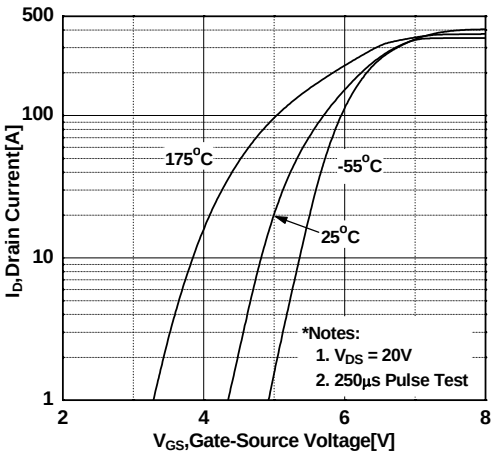


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

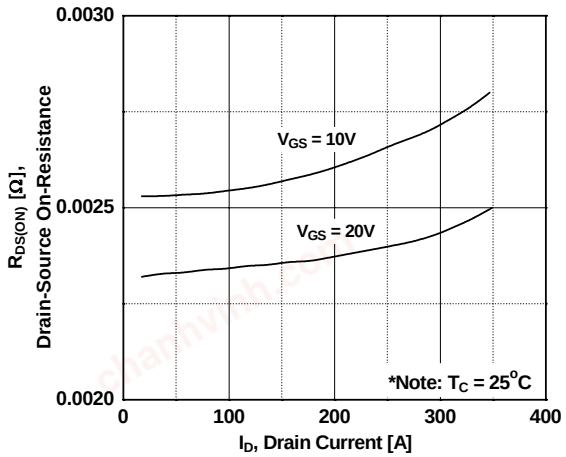


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

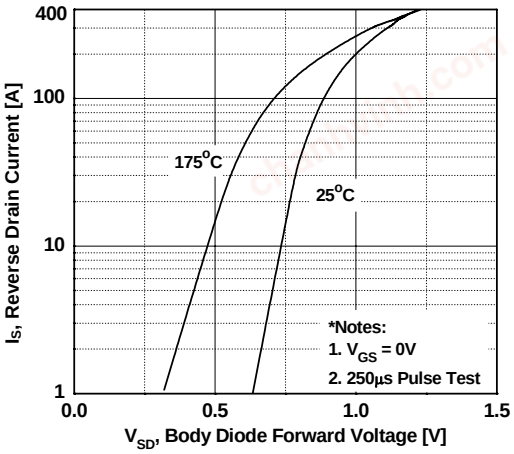


Figure 5. Capacitance Characteristics

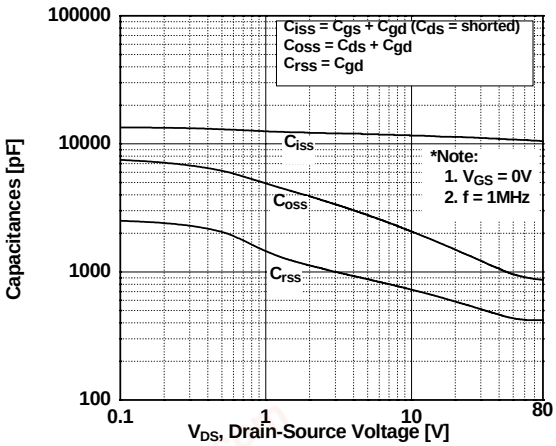
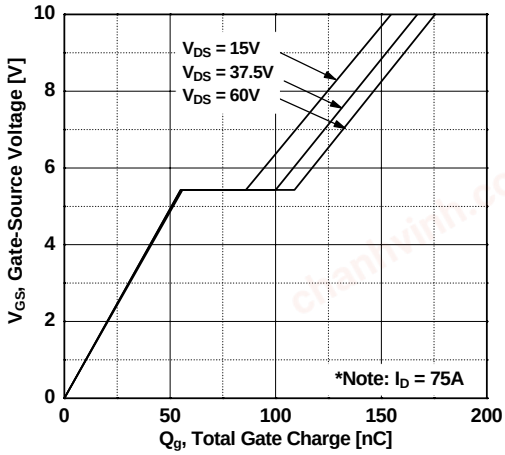


Figure 6. Gate Charge Characteristics



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Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

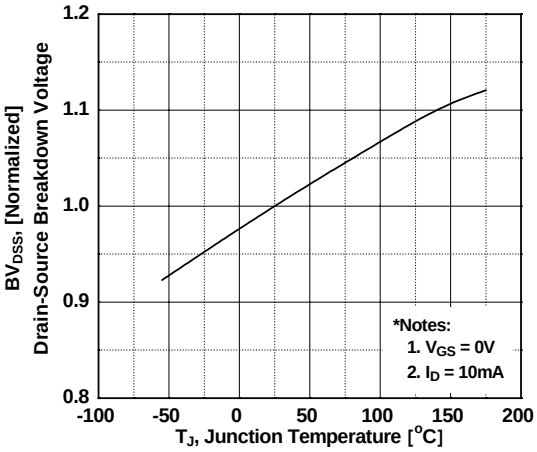


Figure 8. On-Resistance Variation vs. Temperature

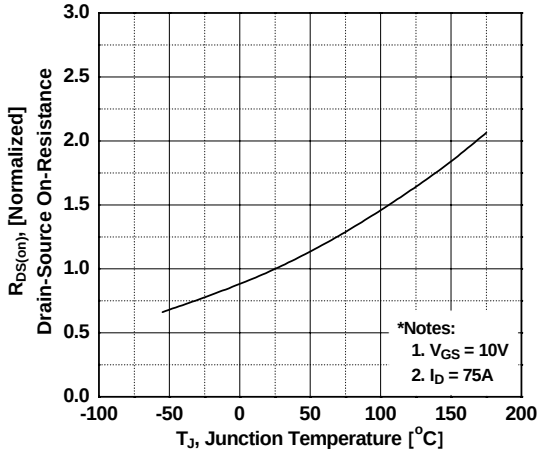


Figure 9. Maximum Safe Operating Area

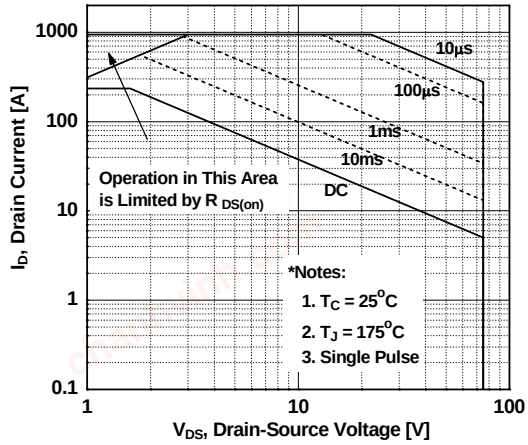


Figure 10. Maximum Drain Current vs. Case Temperature

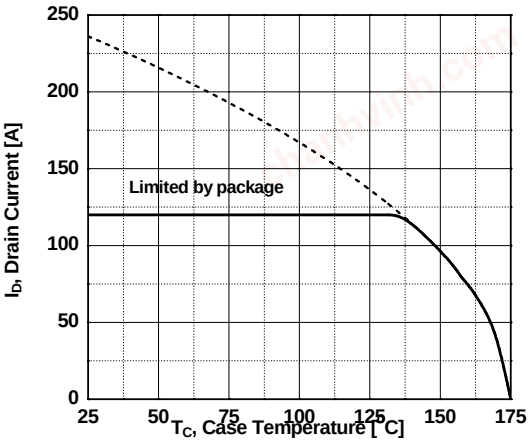
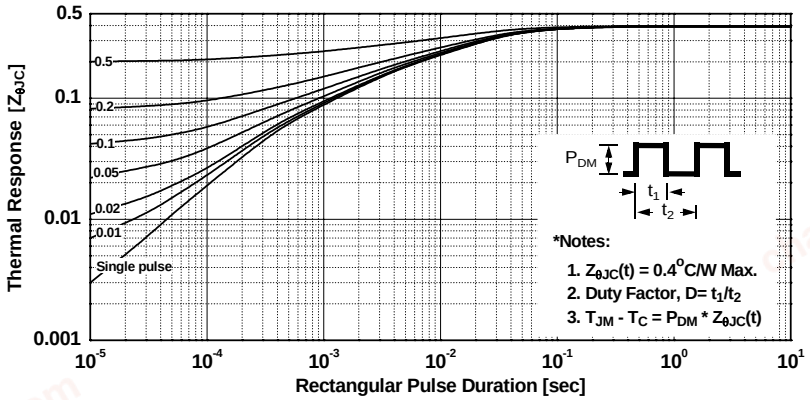
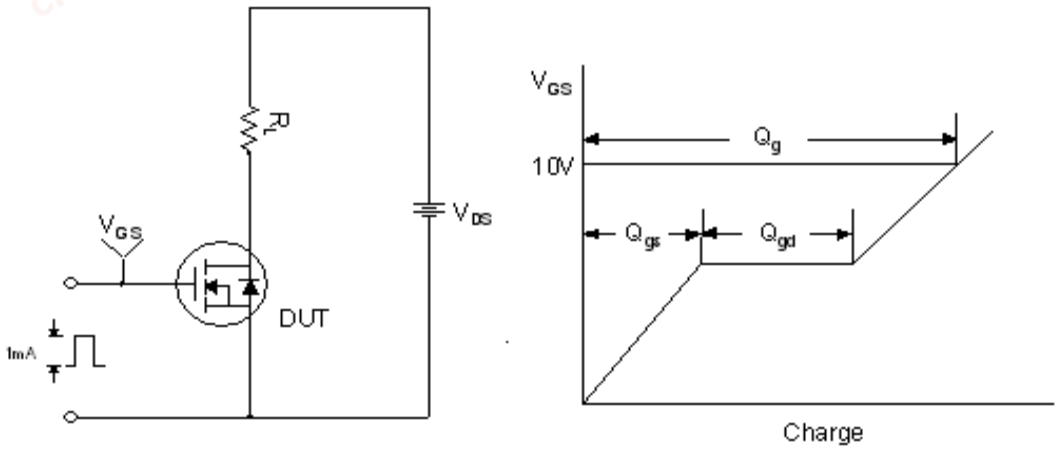


Figure 11. Transient Thermal Response Curve

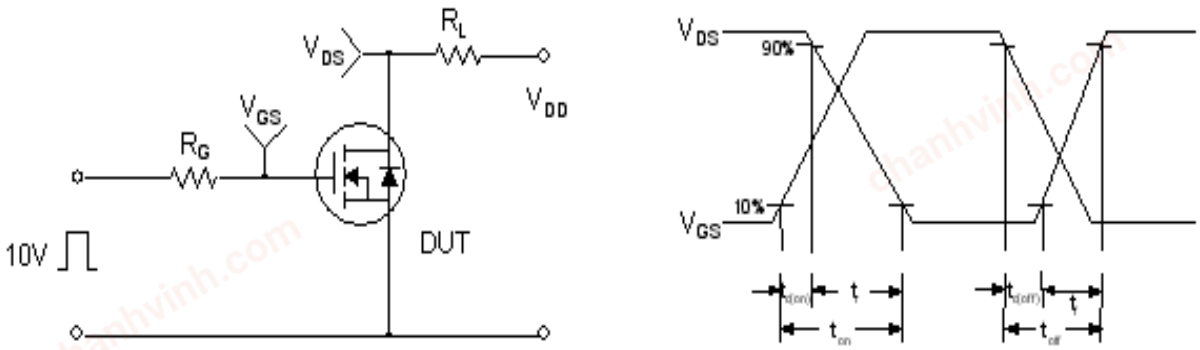


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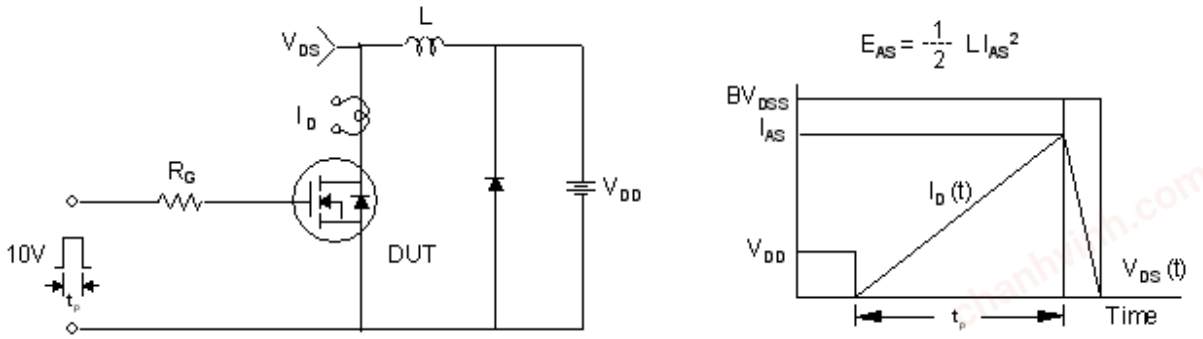
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

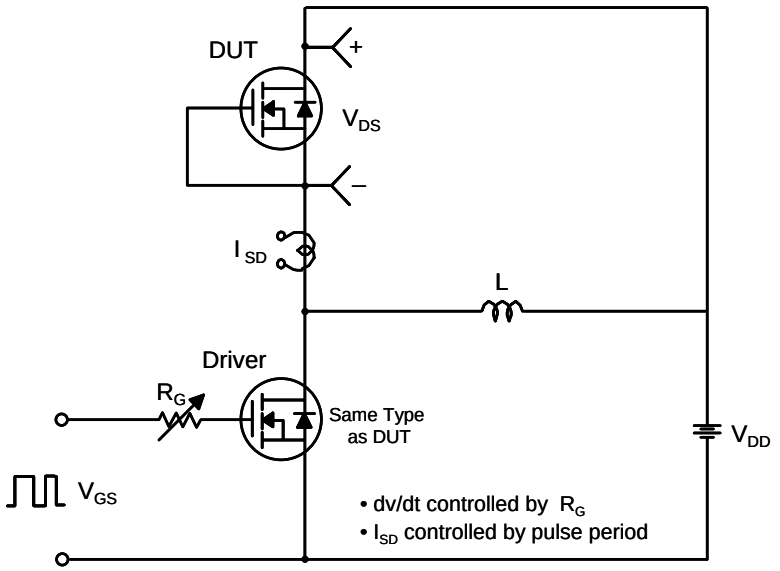


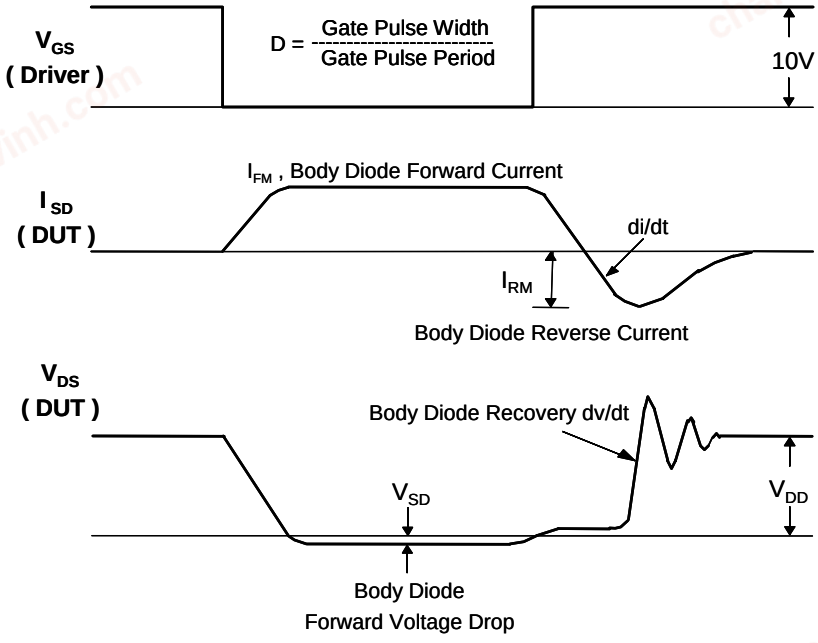
Unclamped Inductive Switching Test Circuit & Waveforms



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Peak Diode Recovery dv/dt Test Circuit & Waveforms

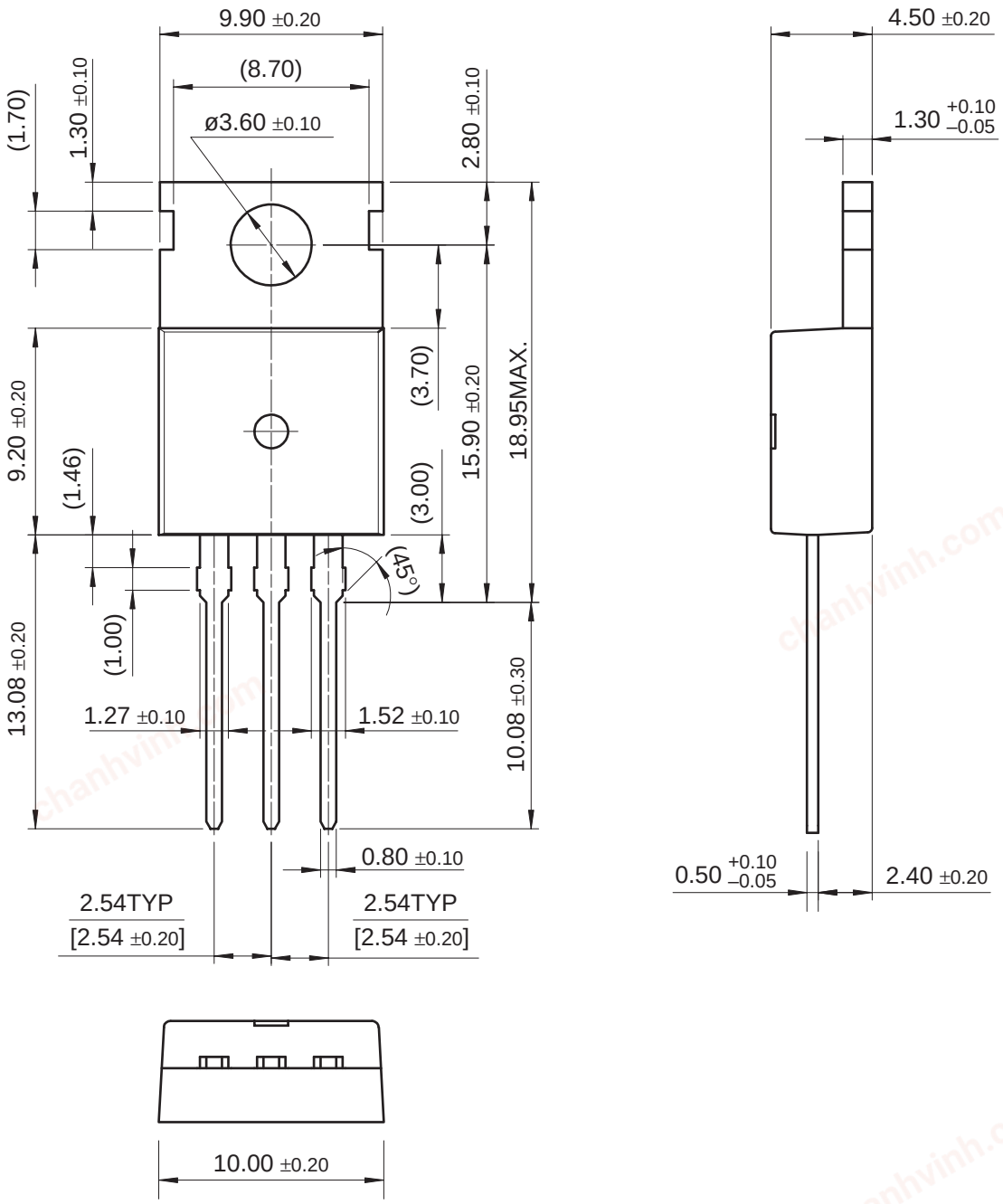




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Mechanical Dimensions

TO-220



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